

Figure 1. In situ spectroscopic ellipsometry results for β -Ga₂O₃ etching at various stage voltages. Etch rates can be tuned based on voltage applied to stage.

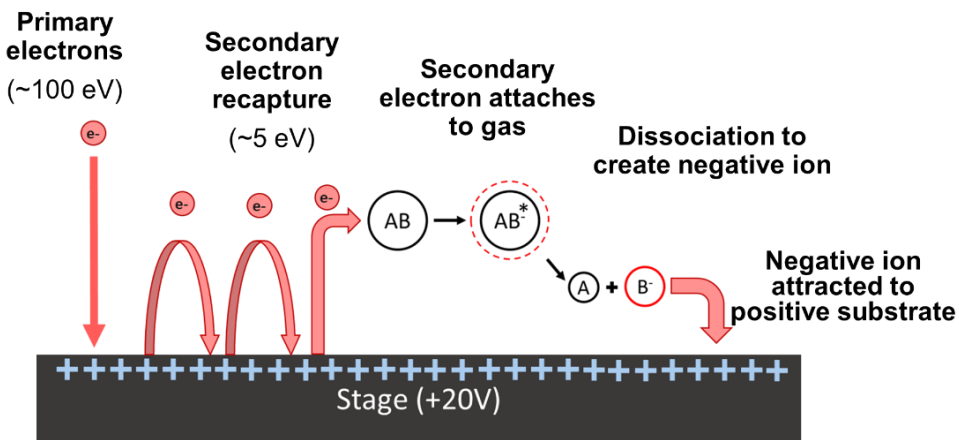


Figure 2. Proposed mechanism for etch rate enhancement resulting from positive stage voltage. Dissociative electron attachment creates a negative ion that is attracted to the positive potential on stage.